Product Preview Internally Clamped N-Channel IGBT

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features Gate–Emitter ESD protection, Gate Collector Over– Voltage Protection from monolithic circuitry for usage as an Ignition Coil Driver.

- Temperature Compensated Gate Collector Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability





MGP20N63CL



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	CLAMPED	Vdc
Collector–Gate Voltage	VCER	CLAMPED	Vdc
Gate–Emitter Voltage	VGE	CLAMPED	Vdc
Collector Current — Continuous	IC	20	Adc
Total Power Dissipation Derate above 25°C	PD	180 1.4	Watts W/°C
Operating and Storage Temperature Range	Tj, T _{stg}	-55 to 175	°C
UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS (TJ < 150°C	;)		
Single Pulse Collector–to–Emitter Avalanche Energy $V_{CC} = 50 \text{ V}, \text{ V}_{GE} = 5.0 \text{ V}, \text{ PEAK I}_{L} = 14.2 \text{ A}, \text{ L} = 3.0 \text{ mH}, \text{ Starting T}_{J} = 25^{\circ}\text{C}$ $V_{CC} = 50 \text{ V}, \text{ V}_{GE} = 5.0 \text{ V}, \text{ PEAK I}_{L} = 10 \text{ A}, \text{ L} = 3.0 \text{ mH}, \text{ Starting T}_{J} = 150^{\circ}\text{C}$	E _{AS}	650 350	mJ
THERMAL CHARACTERISTICS			
Thermal Resistance — Junction-to-Case — Junction-to-Ambient	R _θ JC R _θ JA	0.8 40	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	Т	260	°C

This document contains information on a new product. Specifications and information herein are subject to change without notice.



MGP20N63CL

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Cha	acteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•				
Collector–Emitter Clamp Voltage (I _C = 1.0 mA, T _J = -40°C to 175°	C)	V _(BR) CES	_	630	_	Vdc
Zero Gate Voltage Collector Current (V _{CE} = 500 V, V _{GE} = 0 V) (V _{CE} = 500 V, V _{GE} = 0 V, T _J = 15	50°C)	ICES		_	100 2000	μAdc
Gate–Emitter Clamp Voltage (IG = 5.0 mA)		V _(BR) GES	17	_	22	Vdc
Gate–Emitter Leakage Current (VGE = 10 V)		IGES	_	_	20	μAdc
Gate-Resistor		RG	—	400	—	Ω
ON CHARACTERISTICS (1)						•
Gate Threshold Voltage (VGE = VCE, IC = 1.0 mA) Threshold Temperature Coefficier	t (Negative)	VGE(th)		1.7 4.4		Vdc mV/°C
Collector-to-Emitter On-Voltage ($V_{GE} = 3.5 \text{ V}, I_C = 6.0 \text{ A}$) ($V_{GE} = 4.0 \text{ V}, I_C = 10 \text{ A}, T_J = 150 \text{ A}$)	°C)	VCE(on)		1.6 1.7		Volts
Forward Transconductance $(V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ A})$		9fe	_	20	_	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{CC} = 15 V, V _{GE} = 0 V, f = 1.0 MHz)	Cies	-	TBD	—	pF
Output Capacitance		C _{oes}	-	TBD	—	1
Transfer Capacitance		C _{res}	—	TBD	—	
SWITCHING CHARACTERISTICS (1)					
Turn–Off Delay Time	$(V_{CC} = 600 \text{ V}, \text{ I}_{C} = 10 \text{ A}, \text{ R}_{G} = 1.0 \text{ k}\Omega, \text{ L} = 300 \mu\text{H})$	^t d(off)	-	TBD	—	μSec
Fall Time		t _f	—	TBD	—	
Turn–On Delay Time	$(V_{CC} = 10 V, I_C = 10 A, R_G = 1.0 k\Omega, R_L = 1.0 Ω)$	^t d(on)	—	TBD	—	μSec
Rise Time		tr	—	TBD	—	
Gate Charge		QT	—	TBD	—	nC
		Q ₁	-	TBD	-	1
		Q ₂	—	TBD	—	1

(1) Pulse Test: Pulse Width \leq 300 μ S, Duty Cycle \leq 2%.

MGP20N63CL

PACKAGE DIMENSIONS



MGP20N63CL

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and was negligent regarding the design or manufacture of the part. Motorola and the such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and the such unintended or unauthorized use, even if such claim alleges that Motorola was negligent rega

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 1–303–675–2140 or 1–800–441–2447

Customer Focus Center: 1-800-521-6274

 Mfax™: RMFAX0@email.sps.mot.com
 - TOUCHTONE 1–602–244–6609

 Motorola Fax Back System
 - US & Canada ONLY 1–800–774–1848

 - http://sps.motorola.com/mfax/

HOME PAGE: http://motorola.com/sps/



ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141,

4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

 \diamond

Mfax is a trademark of Motorola, Inc.